

## CLAIMS

1. A plasma display panel (PDP) comprising:
  - a dielectric layer covering a scan electrode and a sustain
  - 5 electrode both formed on a plate; and
  - a protective layer formed on the dielectric layer,
  - wherein the protective layer includes silicon (Si) and nitrogen (N).
- 10 2. The PDP as defined in claim 1, wherein the protective layer is made of magnesium oxide (MgO) including Si of which atoms count in a range from  $5 \times 10^{18}$  pieces/cm<sup>3</sup> to  $2 \times 10^{21}$  pieces/cm<sup>3</sup>, and N of which atoms count in a range from  $1 \times 10^{18}$  pieces/cm<sup>3</sup> to  $8 \times 10^{21}$  pieces/cm<sup>3</sup>.
- 15 3. A method of manufacturing a plasma display panel (PDP), the method comprising the steps of:
  - forming a dielectric layer to cover a scan electrode and a
  - sustain electrode both formed on a plate; and
  - forming a protective layer on the dielectric layer,
  - 20 wherein the step of forming the protective layer is a process for forming a film that uses material of the protective layer, which material includes silicon (Si) and nitrogen (N).
- 25 4. The method of manufacturing a PDP as defined in claim 3, wherein the material of the protective layer is made of magnesium oxide (MgO) including Si and N,
  - wherein a concentration of the Si falls within a range from 7
  - weight ppm to 8000 weight ppm, and a concentration of the N falls within a
  - range from 4 weight ppm to 6000 weight ppm.

5     5. The method of manufacturing a PDP as defined in claim 3, wherein the material of the protective layer is made of magnesium oxide (MgO) including silicon nitride ( $\text{Si}_3\text{N}_4$ ) of which concentration falls within a range from 10 weight ppm to 15000 weight ppm.

10     6. Material of a protective layer of a plasma display panel, wherein the protective layer is formed on a dielectric layer which covers a scan electrode and a sustain electrode both formed on a plate, wherein the material includes silicon (Si) and nitrogen (N).

15     7. The material as defined in claim 6, which material is made of magnesium oxide (MgO) including Si and N, wherein a concentration of the Si falls within a range from 7 weight ppm to 8000 weight ppm, and a concentration of the N falls within a range from 4 weight ppm to 6000 weight ppm.

20     8. The material as defined in claim 6, which material is made of magnesium oxide (MgO) including silicon nitride ( $\text{Si}_3\text{N}_4$ ) of which concentration falls within a range from 10 weight ppm to 15000 weight ppm.